

Improved geometrical correction in micro four-point probe technique with three omega correction



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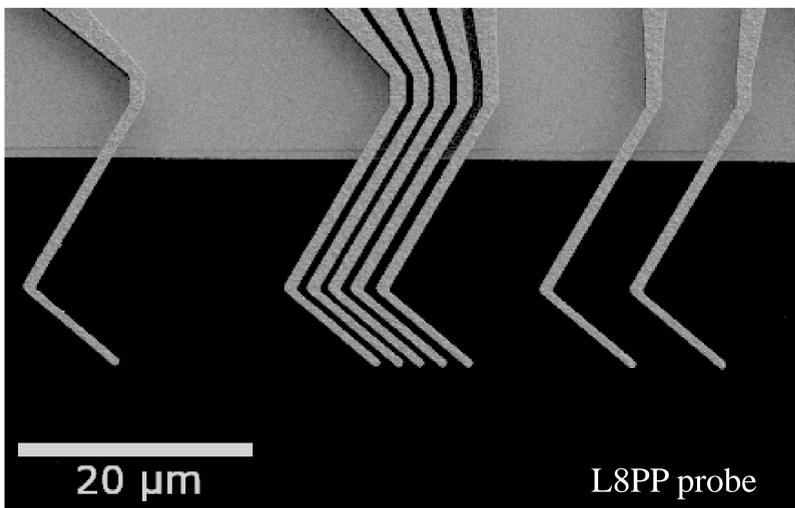
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1. Joule heating in M4PP

- The accuracy of a micro four-point probe (M4PP) measurement depends on sample resistivity and geometry, electrode separation [1] and second order effects such as Joule heating.
- Joule heating ($\propto RI^2$) can change the sample resistance, consequently introducing measurement errors in sheet resistance [2].

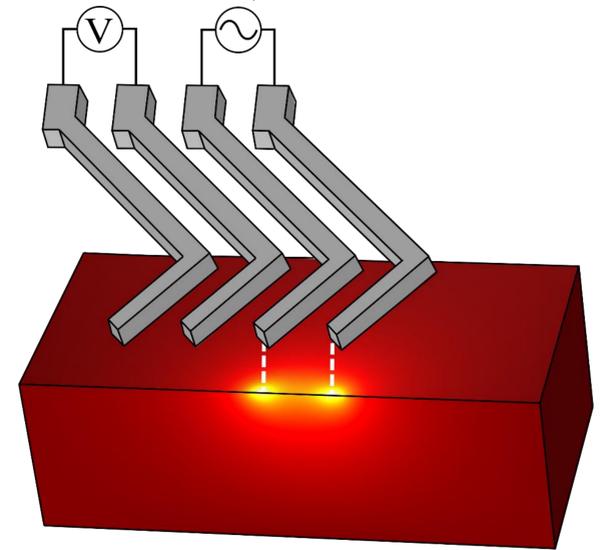


3. Investigation of Joule heating effects using finite element method (FEM)

CAPRES microRSP-A301



COMSOL (electrical + heat transfer)

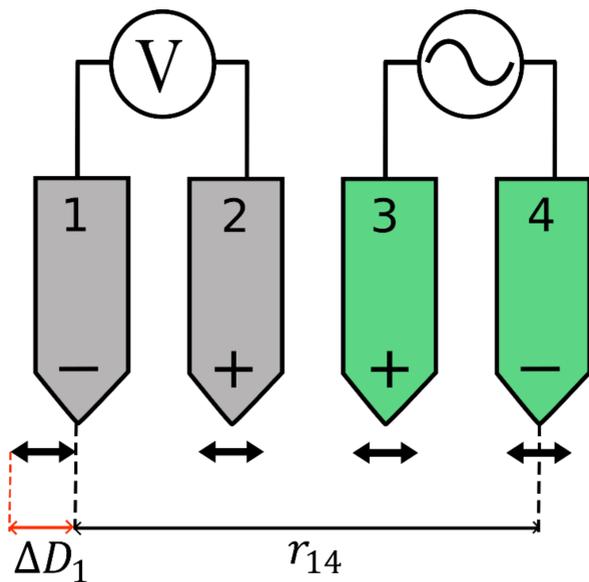


Bulk silicon parameters

| Dopant | Resistivity (Ω cm) | Seebeck coefficient (μ V K ⁻¹) | Thermal conductivity (W m ⁻¹ K ⁻¹) | TCR (% K ⁻¹) |
|--------|----------------------------|---|--|--------------------------|
| Boron | 0.0132 | 632 | 128.3 | 0.18 |

2. Geometrical error are crucial for accurate M4PP results

$$V_{model} = \frac{I(t)\rho}{2\pi} \left(\frac{1}{r_{13}} - \frac{1}{r_{14}} + \frac{1}{r_{23}} - \frac{1}{r_{24}} \right)$$



4. Improved accuracy of geometry via 3ω correction

- 3ω correction:** removal of the current dependency from the measured first harmonic voltage using the third harmonic voltage [2].

$$\chi^2 = \sum_{i=1}^N \left(\frac{V_{i,mod}(X, \beta_i)}{V_{1,mod}} - \frac{V_{i,meas}}{V_{1,meas}} \right)^2$$

$$\Delta D = \text{abs}(X_{regress} - X_{nominal}).$$

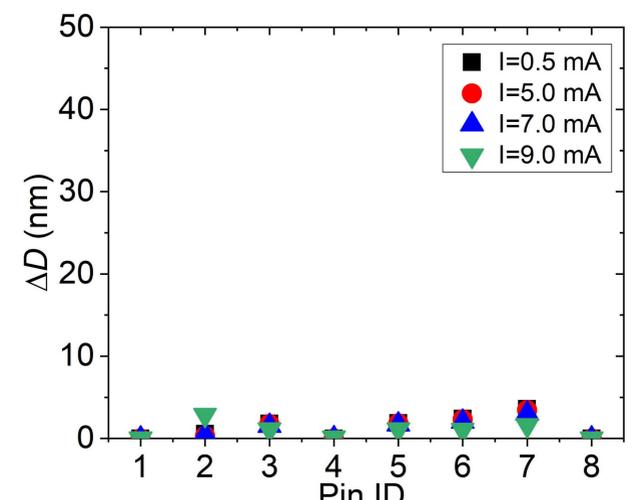
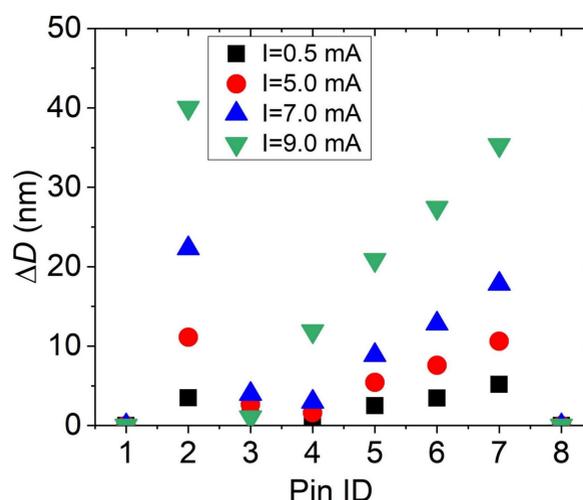
$$V_{corr} = V_{1\omega} - 3V_{3\omega}$$

- Relative error in resistivity up to 0.6% at highest current value
- Position error up to 42 nm

- Relative error in resistivity up to 2 ppm

Uncorrected

3ω corrected



5. Conclusion

- Effect of Joule heating on position-correction analysis with and without 3ω correction of data, the former leads to tenfold improvement of pin position.
- Joule heating can also be utilized to characterize thermal properties of the materials.

Acknowledgments

